



Description

The XPX3N3U8RD uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

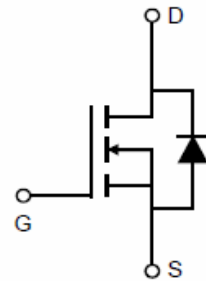
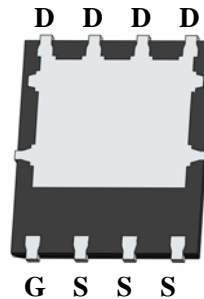
Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

$V_{DS} = 30V, I_D = 80A$

$R_{DS(ON)} = 3.8m\Omega$ (typ) @ $V_{GS} = 10V$

$R_{DS(ON)} = 4.5m\Omega$ (typ) @ $V_{GS} = 4.5V$



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
XPX3N3U8RD	XPX3N3U8RD	DFN5X6-8L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	80	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	60	A
Pulsed Drain Current	I_{DM}	250	A
Maximum Power Dissipation	P_D	68	W
Derating factor		0.6	W/ $^\circ C$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$
Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	2.5	$^\circ C/W$

Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	30	35	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.5	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	3.7	4.5	mΩ
		V _{GS} =4.5V, I _D =20A	-	4.5	5.5	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =20A	-	70	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	2500	-	PF
Output Capacitance	C _{oss}		-	448	-	PF
Reverse Transfer Capacitance	C _{rss}		-	339	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, R _L =15Ω V _{GS} =10V, R _G =2.5Ω	-	13	-	nS
Turn-on Rise Time	t _r		-	16	-	nS
Turn-Off Delay Time	t _{d(off)}		-	45	-	nS
Turn-Off Fall Time	t _f		-	17	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =20A, V _{GS} =10V	-	71	-	nC
Gate-Source Charge	Q _{gs}		-	7.8	-	nC
Gate-Drain Charge	Q _{gd}		-	18.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =20A	-	-	1.4	V
Diode Forward Current (Note 2)	I _S		-	-	60	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 20A di/dt = 100A/μs (Note 3)	-	25	-	nS
Reverse Recovery Charge	Q _{rr}		-	38	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics (Curves)

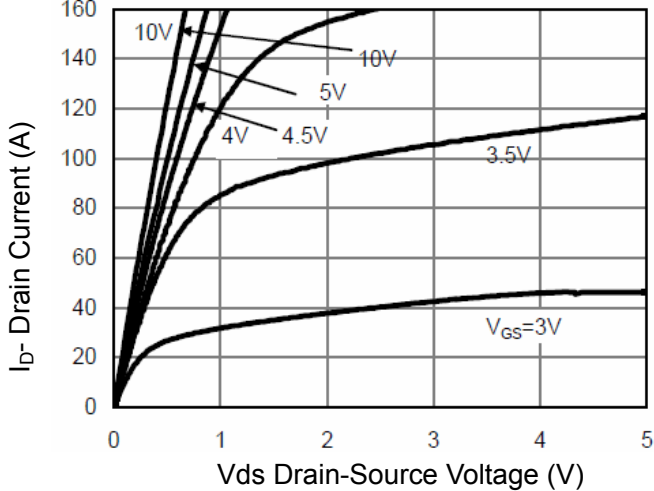


Figure 1 Output Characteristics

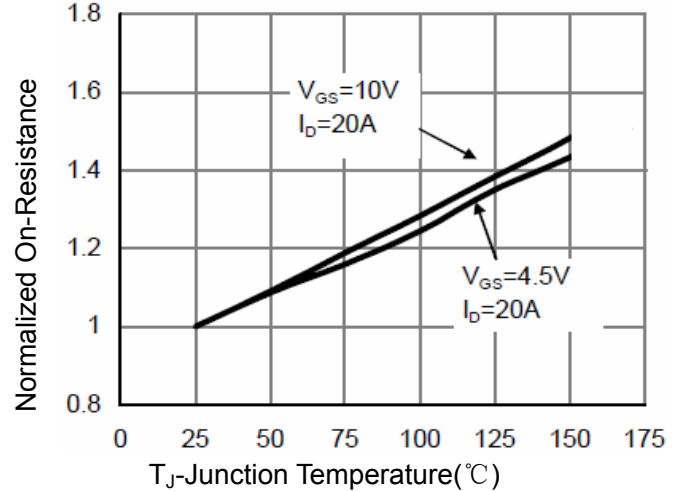


Figure 4 Rdson-Junction Temperature

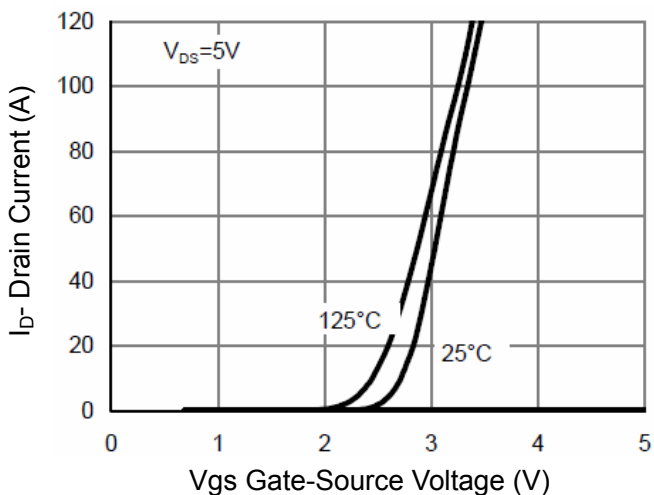


Figure 2 Transfer Characteristics

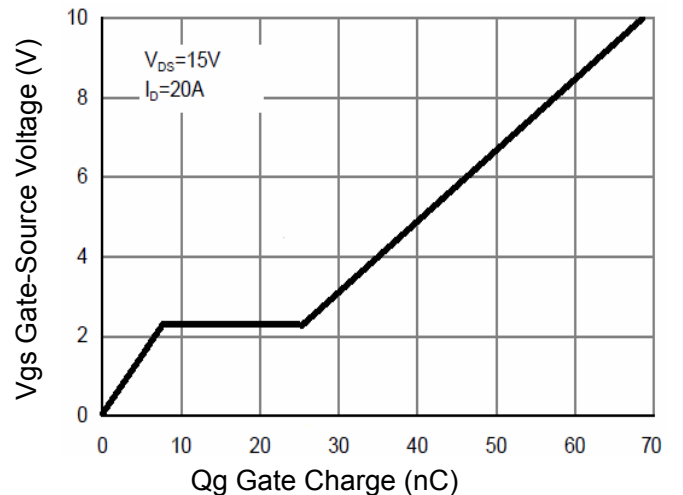


Figure 5 Gate Charge

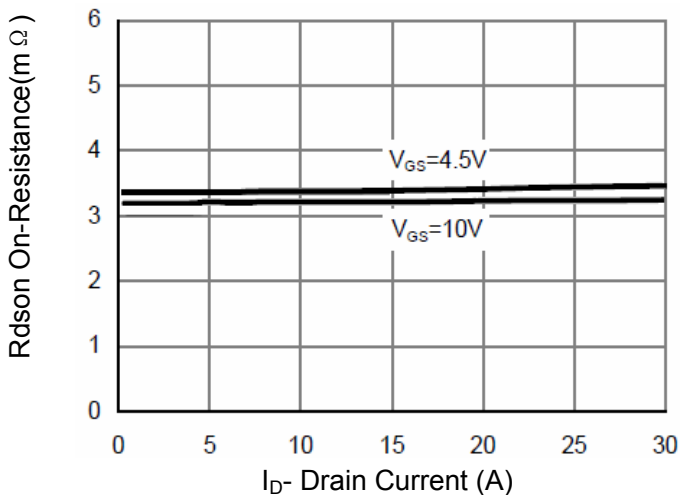


Figure 3 Rdson- Drain Current

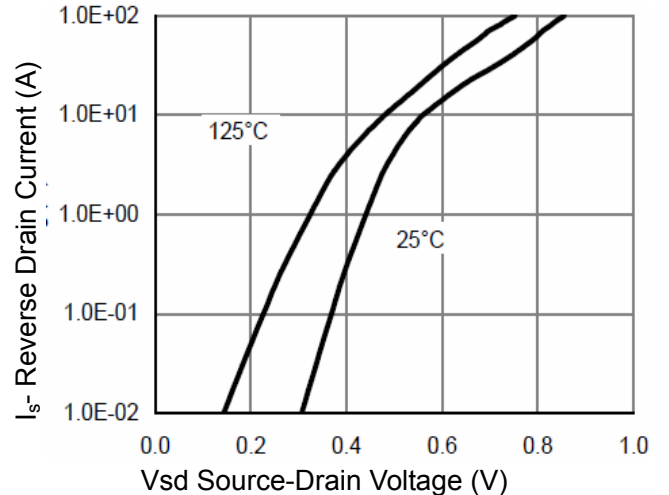


Figure 6 Source- Drain Diode Forward

30V N-Channel Enhancement Mode Power MOSFET

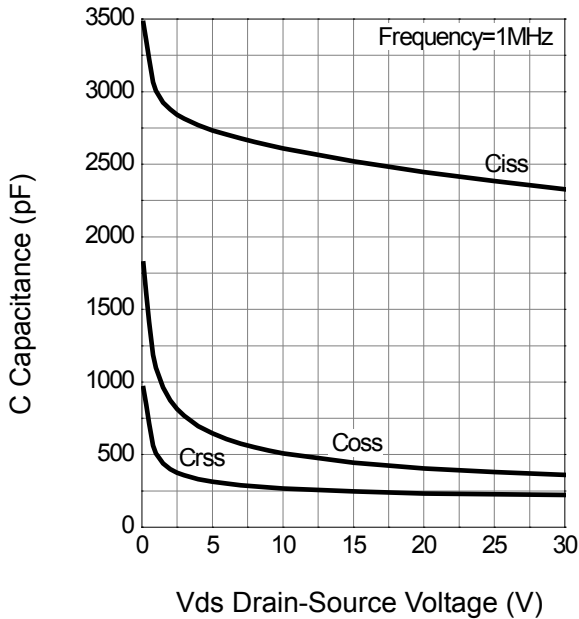


Figure 7 Capacitance vs Vds

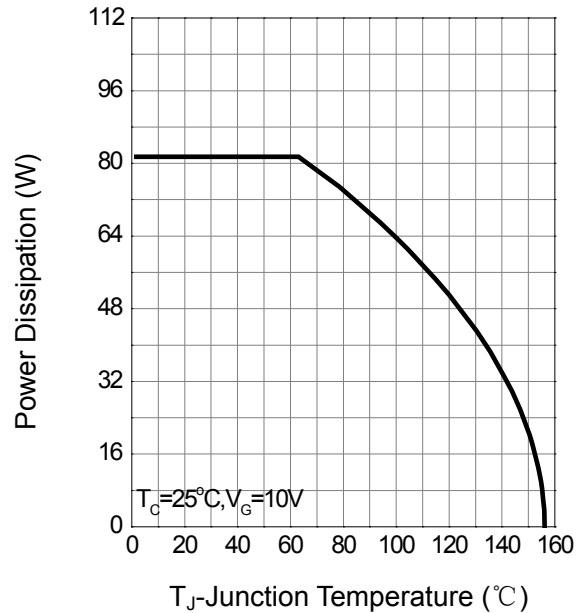


Figure 9 Power De-rating

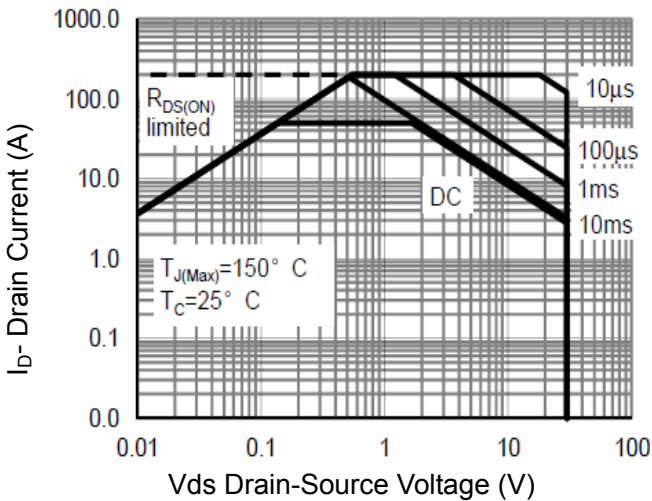


Figure 8 Safe Operation Area

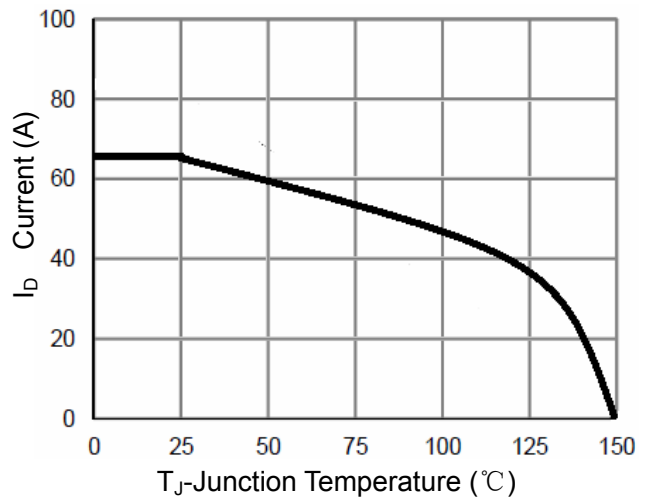


Figure 10 Current- Junction Temperature

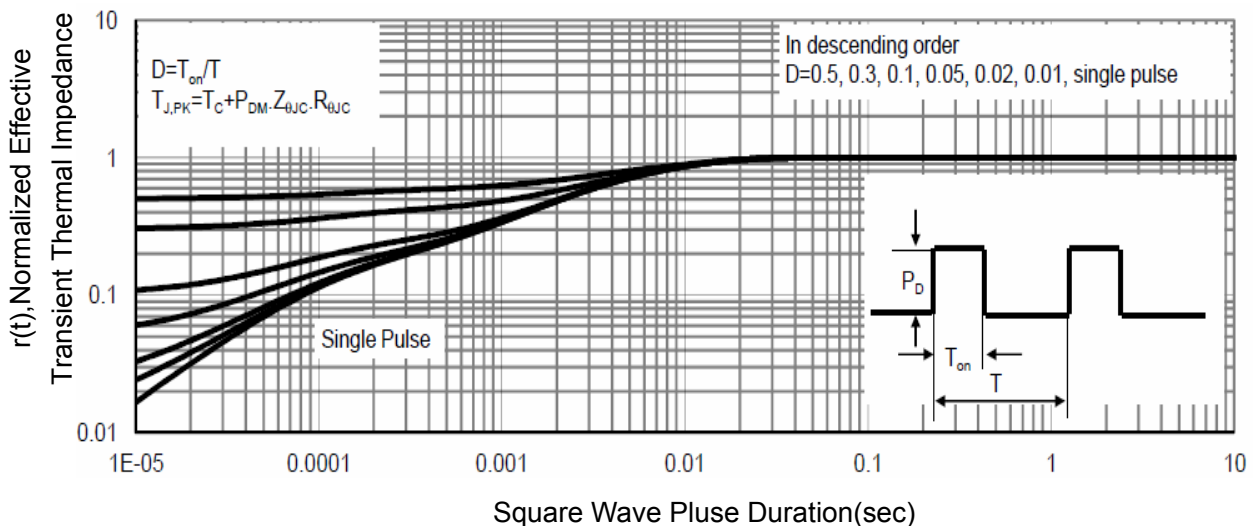
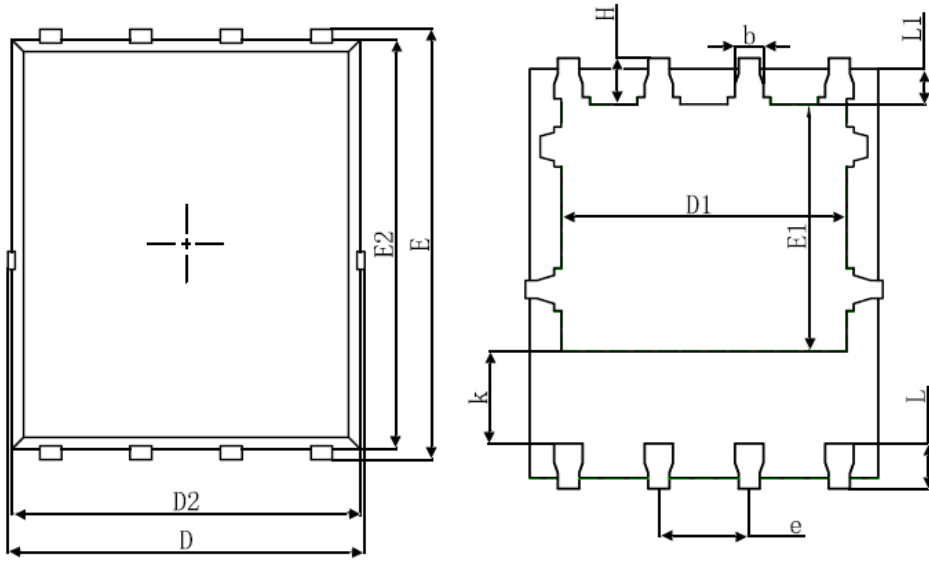
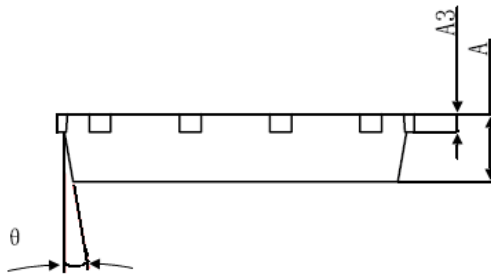


Figure 11 Normalized Maximum Transient Thermal Impedance



Top View
[顶视图]

Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	8°	12°	8°	12°

30V N-Channel Enhancement Mode Power MOSFET

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C ±5°C	5sec ±1sec
Pb-Free device	260°C +0/-5°C	5sec ±1sec



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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